

# SCHOTTKY BARRIER DIODE

●Applications

Low current rectification

●Features

Extremelysmall surface mounting type. (SOD923)

Low  $V_F$

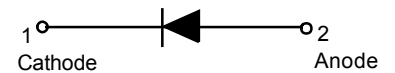
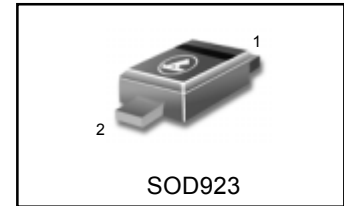
High reliability.

We declare that the material of product compliance with RoHS requirements.

●Construction

Silicon epitaxial planar

**LRB521CS-30T5G**



**DEVICE MARKING AND ORDERING INFORMATION**

Device	Marking	Shipping
LRB521CS-30T5G	F	8000/Tape&Reel

●Absolute maximum ratings (Ta=25°C)

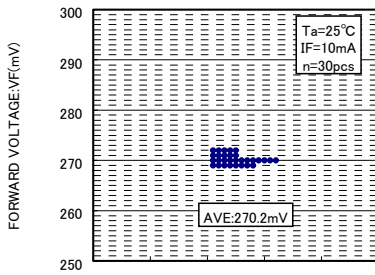
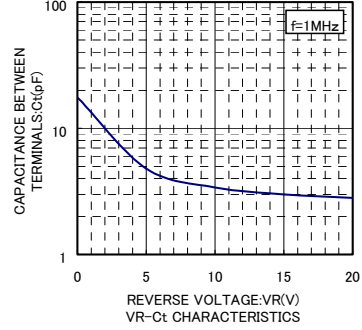
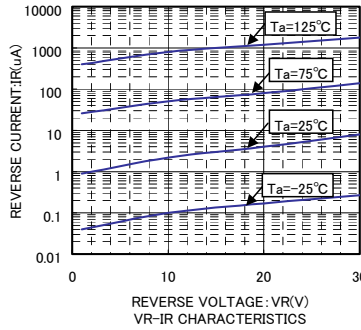
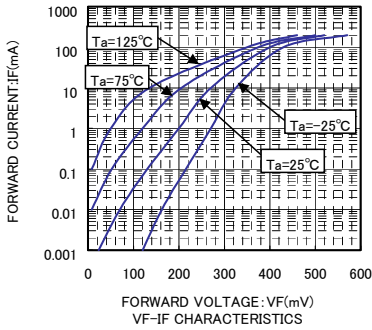
Parameter	Symbol	Limits	Unit
Reverse voltage (DC)	$V_R$	30	V
Average rectifierd forward current	$I_o$	100	mA
Forward current surge peak (60Hz·1cyc)	$I_{FSM}$	500	mA
Junction temperature	$T_j$	125	°C
Storage temperature	$T_{stg}$	-40 to +125	°C

●Electrical characteristic (Ta=25°C)

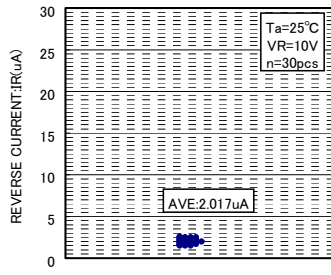
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward vpltage	$V_F$	-	-	0.35	V	$I_F=10mA$
Forward vpltage	$V_F$	-	-	0.4	V	$I_F=20mA$
Reverse current	$I_R$	-	-	10	$\mu A$	$V_R=10V$

**LRB521CS-30T5G**

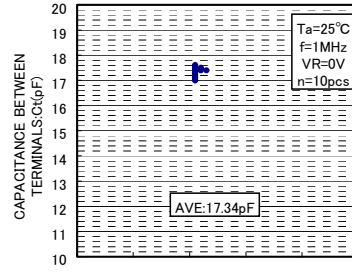
● **Electrical characteristic curves**



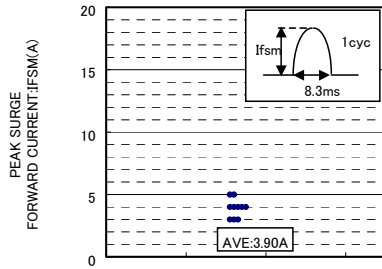
VF DISPERSION MAP



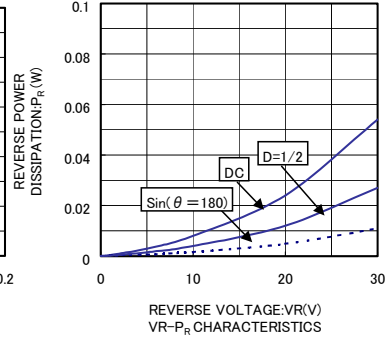
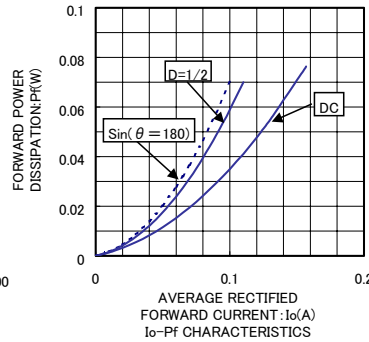
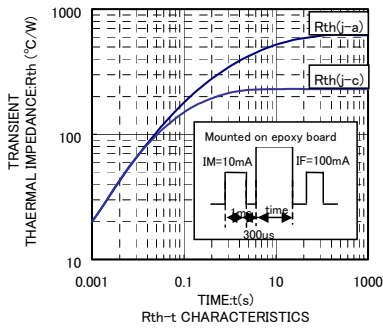
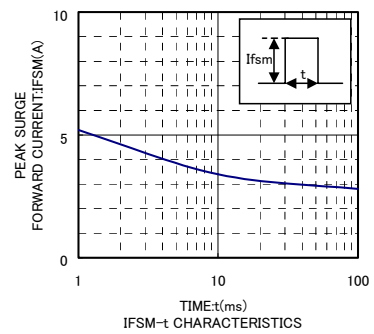
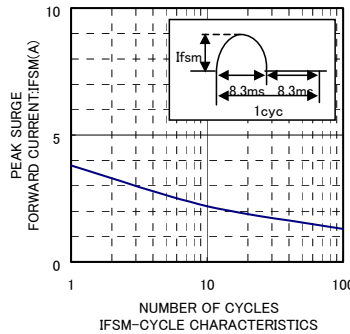
IR DISPERSION MAP

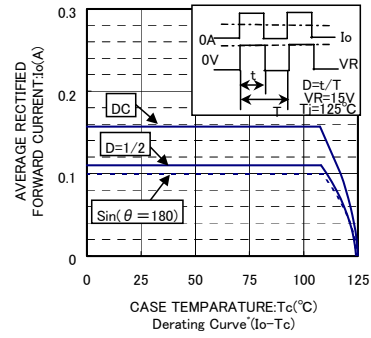
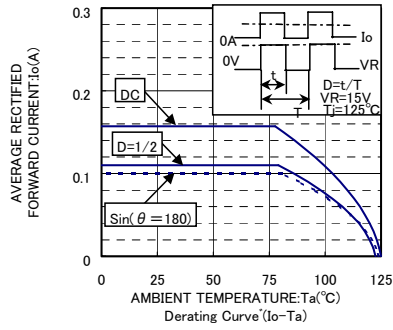


Ct DISPERSION MAP



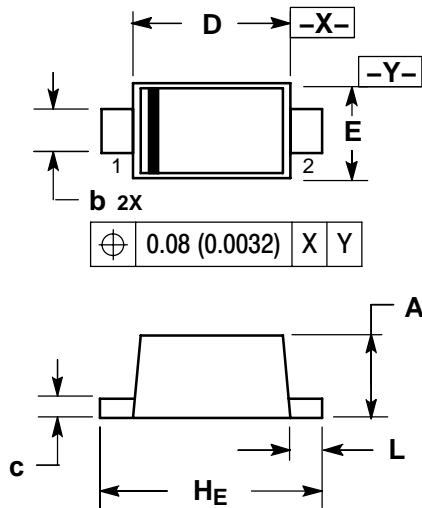
IFSM DISERSION MAP



**LRB521CS-30T5G**
**Electrical characteristic curves ( $T_a=25^{\circ}\text{C}$ )**


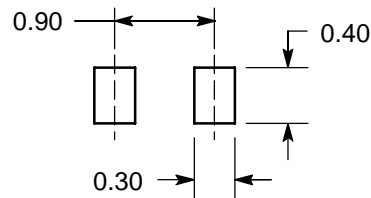
LRB521S-30T5G

SOD-923



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.34	0.39	0.43	0.013	0.015	0.017
b	0.15	0.20	0.25	0.006	0.008	0.010
c	0.07	0.12	0.17	0.003	0.005	0.007
D	0.75	0.80	0.85	0.030	0.031	0.033
E	0.55	0.60	0.65	0.022	0.024	0.026
HE	0.95	1.00	1.05	0.037	0.039	0.041
L	0.05	0.10	0.15	0.002	0.004	0.006

SOLDERING FOOTPRINT\*



DIMENSIONS: MILLIMETERS